

L Number	Hits	Search Text	DB	Time stamp
1	104	polymer and defect and photoresist and mask and expose and bake	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 08:26
13	26693	((hot adj deionized adj water) (hot and DIW) (hot adj DI adj water) (hot adj DI water) and rinse and temperature)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 08:43
19	26669	((hot adj deionized adj water) (hot adj DIW) (hot adj DI adj water) (hot adj DI water) and rinse and temperature)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 11:59
25	104	((hot adj deionized adj water) and rinse and temperature)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 08:44
31	3	((hot adj DIW) and rinse and temperature)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 08:45
43	45	((hot adj DI adj water) and rinse and temperature and heat\$?)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 10:13
59	8	((hot adj DI) and deionized and (developer developed) and photoresist and temperature and (heat heater))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 11:17
65	235	(hot and (DI DIW) and water and deionized and (developer developed) and photoresist and temperature and (heat heater))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 11:19
71	48	((hot adj deionized adj water) and (hot adj DIW) (hot adj DI adj water) and rinse and temperature)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 13:14
77	1	development adj related adj defect	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 13:15
83	499	development adj defect	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 13:15
89	69	(development adj defect) and photoresist	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 13:42
95	1		USPAT	2002/06/04 13:39
96	1		USPAT	2002/06/04 13:41
97	2	(development adj defect) and photoresist and blob	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 13:42
103	26	(development adj defect) and photoresist and water	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 13:43
109	499	((development adj defect) (post-development adj defect) and photoresist and water)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 14:02

-	0	(polymer and blob) and photoresist and mask and expos&? and bak&? and develop&? and hea&? and ((deionized adj water) (hot and DIW)) and rins&?	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/03 16:04
-	0	((polymer and blob) and photoresist and mask and expos&? and bak&? and develop&? and hea&? and ((deionized adj water) (hot and DIW))and rins&?)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/03 16:05
-	0	((polymer and blob) and photoresist and mask and expos&? and bak&? and develop&? and heat&? and ((deionized adj water) (hot and DIW)and rins&?)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/03 16:06
-	0	((polymer and defect) and photoresist and mask and expos&? and bak&? and develop&? and heat&? and ((deionized adj water) (hot and DIW)and rins&?)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/03 16:10
-	38	(438/727).CCLS.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/03 16:08
-	0	polymer and defect and photoresist and mask and expos&? and bak&?	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/03 16:09
-	6	((polymer and defect) and photoresist and mask and expose and bake and develop and heat and ((deionized adj water) (hot and DIW) and rinse)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/04 08:39
-	0	((polymer and blob) and photoresist and mask and expose and bake and develop and heat and ((deionized adj water) (hot and DIW) and rinse)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/03 16:19
-	15	(polymer and photoresist and mask and expose and bake and develop and heat and ((deionized adj water) (hot and DIW) and rinse)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/06/03 16:20